

EPROMs, EEPROMs & Flash Memory

210896

EPROMs and PROMs				Vcc =	Price Each						
Mfr.	Pins	Pkg	Description	5V ±	Mfrs. List No.	Order Code	1+	25+	100+	250+	+
64K											
27C64	ST	28	DIL 64K (8K × 8) EPROM - 100ns Access, 12.5V VPP	10%	M27C64A-10F1	366-3358▲	288.00	263.00	242.00	223.00	--
27C64	ST	28	DIL 64K (8K × 8) EPROM - 100ns Access, 12.5V VPP	10%	M27C64A-10F1	109-4265●	291.00	250.00	218.00	194.00	--
27C64	ST	28	DIL 64K (8K × 8) CMOS EPROM - 150ns Access, 12.5V VPP	10%	M27C64A-15F1	594-489▲	271.00	233.00	215.00	203.00	--
27C64	ST	28	DIL 64K (8K × 8) CMOS EPROM - 200ns Access, 12.5V VPP	10%	M27C64A-20F1	270-416▲	271.00	248.00	228.00	210.00	--
256K											
256	ATM	32	PLCC 256K (32K × 8) CMOS OTP EPROM - 70ns Access	10%	AT27C256R-70JU	109-5779●	94.00	77.00	61.00	60.00	--
256	ATM	28	DIL 256K (32K × 8) CMOS OTP EPROM - 70ns Access	10%	AT27C256R-70PU	109-5781●	94.00	77.00	61.00	60.00	--
27C256	ST	28	DIL 256K (32K × 8) CMOS EPROM - 100ns Access, 12.75V VPP	10%	M27C256B-10F1	302-5147▲	194.00	177.00	163.00	151.00	--
27C256	ST	28	DIL 256K (32K × 8) CMOS EPROM - 150ns Access, 12.75V VPP	10%	M27C256B-15F1	112-5431●	198.00	181.00	167.00	149.00	--
27C256	ST	28	DIL 256K (32K × 8) CMOS EPROM - 70ns Access, 12.75V VPP	5%	M27C256B-70XF1	597-454▲	211.00	192.00	178.00	163.00	--
512K											
27C512	ST	28	DIL 512k (64k × 8) CMOS EPROM - 45ns Access, 12.75V VPP	5%	M27C512-45XF1	366-3334▲	284.00	260.00	239.00	220.00	--
27C512	ST	32	PLCC 512k (64k × 8) CMOS OTP PROM, 90ns Access, 12.75 V VPP	10%	M27C512-90C1	121-8315●	233.00	190.00	153.00	--	--
27C512	ST	28	DIL 512k (64k × 8) CMOS EPROM 90ns Access, 12.75V VPP	10%	M27C512-90F6	109-4264●	225.00	193.00	179.00	168.00	--
27C512	ST	28	DIL 512K (64K × 8) CMOS EPROM - 150ns Access, 12.75V VPP	10%	M27C512-15F1	394-713▲	202.00	184.00	170.00	156.00	--
27C512	ST	28	DIL 512K (64K × 8) CMOS EPROM - 150ns Access, 12.75V VPP (IND TEMP)	10%	M27C512-15F6	705-251▲	202.00	184.00	170.00	156.00	--
27C512	ST	28	DIL 512K (64K × 8) CMOS EPROM - 150ns Access, 12.75V VPP (IND TEMP)	10%	M27C512-15F6	113-2010●	202.00	184.00	160.00	151.00	--
1Mb											
27C1001	ST	32	DIL 1Mb (128K × 8) CMOS EPROM - 120ns Access, 12.75V VPP	10%	M27C1001-12F1	597-296▲	288.00	263.00	243.00	223.00	--
27C1001	ST	32	DIL 1Mb (128K × 8) CMOS EPROM - 120ns Access, 12.75V VPP	10%	M27C1001-12F1	113-2006●	288.00	248.00	216.00	192.00	--
27C1001	ST	32	DIL 1Mb (128K × 8) CMOS EPROM - 150ns Access, 12.75V VPP	10%	M27C1001-15F1	395-110▲	259.00	236.00	218.00	194.00	--
27C1001	ST	32	DIL 1Mb (128K × 8) CMOS OTP PROM - 45ns Access, 12.75V VPP	10%	M27C1001-45F1	688-617▲	350.00	300.00	278.00	248.00	--
27C1001	ST	32	DIL 1Mb (128K × 8) CMOS OTP PROM - 45ns Access, 12.75V VPP	10%	M27C1001-45F1	113-2008●	354.00	304.00	265.00	236.00	--
27W101	ST	32	PLCC 1Mb (128K × 8) CMOS OTP PROM - 80ns Access, Low Voltage		M27W101-80K6	366-3152▲	337.00	317.00	309.00	--	--
27W101	ST	32	PLCC 1Mb (128K × 8) CMOS OTP PROM - 80ns Access, Low Voltage		M27W101-80K6	109-4271●	326.00	290.00	273.00	--	--
2Mb											
27C2001	ST	32	DIL 2Mb (256K × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C2001-10B1	333-8101▲	335.00	315.00	297.00	--	--
27C2001	ST	32	DIL 2Mb (256K × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C2001-10B1E	115-9687●	315.00	280.00	264.00	--	--
020	ATM	32	PLCC 2M (256K × 8) CMOS OTP EPROM - 90ns Access	10%	AT27C020-90JU	109-5776●	174.00	142.00	112.00	111.00	--
020	ATM	32	DIL 2M (256K × 8) CMOS OTP EPROM - 90ns Access	10%	AT27C020-90PU	109-5777●	183.00	150.00	117.00	117.00	--
27C2001	ST	32	DIL 2Mb (256K × 8) CMOS EPROM - 100ns Access, 12.75V VPP	10%	M27C2001-10F1	702-523▲	570.00	469.00	345.00	258.00	--
27C2001	ST	32	DIL 2Mb (256K × 8) CMOS EPROM - 150ns Access, 12.75V VPP	10%	M27C2001-15F1	460-059▲	380.00	347.00	320.00	285.00	--
4Mb											
27C4001	ST	32	PLCC 4Mb (512K × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C4001-10C1	302-5196▲	501.00	471.00	455.00	--	--
27C4001	ST	32	PLCC 4Mb (512K × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C4001-10C1	109-4260●	484.00	430.00	402.00	--	--
27C4001	ST	32	DIL 4Mb (512K × 8) CMOS EPROM - 100ns Access, 12.75V VPP	10%	M27C4001-10F1	702-535▲	532.00	457.00	419.00	399.00	--
27C4001	ST	32	DIL 4Mb (512K × 8) CMOS OTP PROM - 120ns Access, 12.75V VPP	10%	M27C4001-12B1	333-8137▲	558.00	525.00	507.00	--	--
27C4001	ST	32	DIL 4Mb (512K × 8) CMOS OTP PROM - 120ns Access, 12.75V VPP	10%	M27C4001-12B1	113-1998●	536.00	476.00	445.00	--	--
27C4001	ST	32	PLCC 4Mb (512K × 8) CMOS OTP PROM - 120ns Access, 12.75V VPP	10%	M27C4001-12C1	597-478▲	501.00	471.00	440.00	--	--
27C4001	ST	32	PLCC 4Mb (512K × 8) CMOS OTP PROM - 120ns Access, 12.75V VPP	10%	M27C4001-12C1	109-4261●	694.00	564.00	452.00	--	--
27C4001	ST	32	DIL 4Mb (512K × 8) CMOS EPROM - 120ns Access, 12.75V VPP	10%	M27C4001-12F1	445-253▲	532.00	486.00	444.00	399.00	--
27C4001	ST	32	DIL 4Mb (512K × 8) CMOS EPROM - 150ns Access, 12.75V VPP	10%	M27C4001-15F1	445-370▲	532.00	457.00	419.00	399.00	--
27C4001	ST	32	DIL 4Mb (512K × 8) CMOS EPROM - 150ns Access, 12.75V VPP	10%	M27C4001-15F1	113-2004●	532.00	457.00	394.00	354.00	--
27C4002	ST	44	PLCC 4Mb (256K × 16) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C4002-10C1	302-5202▲	557.00	526.00	521.00	--	--
27C4002	ST	44	PLCC 4Mb (256K × 16) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C4002-10C1	109-4262●	608.00	540.00	535.00	--	--
27C4002	ST	40	DIL 4Mb (256K × 16) CMOS EPROM - 100ns Access, 12.75V VPP	10%	M27C4002-10F1	688-599▲	698.00	599.00	549.00	523.00	--
27C4002	ST	44	PLCC 4Mb (256K × 16) CMOS OTP PROM - 120ns Access, 12.75V VPP	10%	M27C4002-12C1	302-5214▲	592.00	557.00	521.00	--	--
27C4002	ST	44	PLCC 4Mb (256K × 16) CMOS OTP PROM - 120ns Access, 12.75V VPP	10%	M27C4002-12C1	109-4263●	820.00	648.00	534.00	--	--
27C4002	ST	40	DIL 4Mb (256K × 16) CMOS EPROM - 120ns Access, 12.75V VPP	10%	M27C4002-12F1	702-729▲	698.00	637.00	549.00	523.00	--
27C4002	ST	40	DIL 4Mb (256K × 16) CMOS EPROM - 120ns Access, 12.75V VPP	10%	M27C4002-12F1	113-2009●	714.00	613.00	529.00	476.00	--
27C4002	ST	40	DIL 4Mb (256K × 16) CMOS EPROM - 80ns Access, 12.75V VPP	5%	M27C4002-80XF1	597-491▲	734.00	670.00	611.00	568.00	--
27C4002	ST	40	DIL 4Mb (256K × 16) CMOS EPROM - 45ns Access	5%	M27C4002-45XF1	366-3322▲	1,038.00	868.00	802.00	736.00	--
27C4002	ST	40	DIL 4Mb (256K × 16) CMOS EPROM - 45ns Access	5%	M27C4002-45XF1	113-2002●	1,602.00	1,281.00	950.00	724.00	--
8Mb											
27C801	ST	32	DIL 8Mb (1M × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C801-100B1	333-8174▲	962.00	880.00	831.00	--	--
27C801	ST	32	DIL 8Mb (1M × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C801-100B1	109-4266●	931.00	804.00	759.00	--	--
27C801	ST	32	DIL 8Mb (1M × 8) CMOS EPROM - 100ns Access, 12.75V VPP	10%	M27C801-100F1	688-575▲	1,046.00	874.00	808.00	784.00	--
27C801	ST	32	DIL 8Mb (1M × 8) CMOS EPROM - 100ns Access, 12.75V VPP	10%	M27C801-100F1	113-2007●	1,048.00	876.00	762.00	699.00	--
27C801	ST	32	PLCC 8Mb (1M × 8) CMOS OTP PROM - 100ns Access, 12.75V VPP	10%	M27C801-100K1	333-8186▲	865.00	791.00	771.00	--	--
27C801	ST	32	DIL 8Mb (1M × 8) CMOS EPROM - 120ns Access, 12.75V VPP	10%	M27C801-120F1	688-587▲	1,046.00	928.00	855.00	784.00	--

Semiconductors - Integrated Circuits

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FRAM



Ferroelectric RAM (FRAM) is a RAM based device that uses the ferroelectric effect for a storage mechanism. This is a completely different mechanism than the one used by other non-volatile memories, which use floating gate technology. The ferroelectric effect is the ability of a material to store an electric polarisation in the absence of an applied electric field. The advantage of using this technology is that devices can be produced as pin-for-pin replacements for current memory devices but with the following new features:

- Number of write cycles increased from 100,000 to 10,000,000,000 (10 billion)
- Write speed is the same as read speed (NoDelay™)
- Higher noise immunity as the data does not have to remain stable for the usual 10 milliseconds write period.
- New PCB design is not necessary as the new parts are 'drop in' replacements.
- Can be used as RAM with the added advantage of being non-volatile (NV-RAM), battery back-up not being required.

227405

Parallel				Vcc =	Price Each			
Pins	Pkg	Description	5V ±	Mfrs. List No.	Order Code	1+	10+	100+
4K-bit	8	SOIC 64K (8192 x 8) Serial FRAM - 400KHz bus speed	10%	FM24C04A-G	121-0785●	77.00	70.00	64.00
16K-bit	8	SOIC 64K (8192 x 8) Serial FRAM - 400KHz bus speed	10%	FM24C16A-G	121-0787●	113.00	102.00	94.00
16K-bit	8	SOIC 64K (8192 x 8) 16K (2048 x 8) Serial FRAM memory, 1MHz bus speed, I ² C		FM24CL16-G	121-0794●	135.00	124.00	113.00
16K-bit	28	DIL 64K (8192 x 8) Parallel FRAM	10%	FM1608-120-PG	121-0791●	337.00	308.00	281.00
16K-bit	8	SOIC 64K (8192 x 8) Serial FRAM SPI - 2.1MHz bus speed	10%	FM25C160-G	121-0789●	113.00	102.00	94.00
64 K-bit	28	SOIC 64K (8192 x 8) Parallel FRAM	10%	FM1608-120-SG	120-2307●	309.00	278.00	253.00
64 K-bit	8	SOIC 64K (8192 x 8) Serial FRAM - 1MHz bus speed	10%	FM24C64-G	121-0788●	182.00	169.00	152.00
64 K-bit	8	SOIC 64K (8192 x 8) Serial FRAM SPI - 5MHz bus speed	10%	FM25640-G	121-0790●	182.00	169.00	161.00
64 K-bit	8	SOIC 64K (8192 x 8) 64K (8192 x 8) Serial FRAM memory, 1MHz bus speed, I ² C		FM24CL64-G	121-0795●	204.00	188.00	172.00
64 K-bit	8	SOIC 64K (8192 x 8) 64K (8192 x 8) Serial FRAM memory, high-speed, SPI		FM25CL64-G	121-0796●	204.00	188.00	172.00
256 K-bit	28	DIL 64K (8192 x 8) Parallel FRAM	10%	FM1808-70-PG	121-0792●	576.00	528.00	480.00
256 K-bit	28	SOIC 64K (8192 x 8) Parallel FRAM	10%	FM1808-70-SG	121-0793●	576.00	528.00	480.00
256 K-bit	28	SOIC 64K (8192 x 8) 256K (32768 x 8) Parallel FRAM memory, 70ns acc.		FM18L08-70-SG	121-0797●	645.00	592.00	539.00
256 K-bit	8	SOIC 64K (8192 x 8) 256K (32768 x 8) Serial FRAM memory		FM24C256-G	121-0799●	606.00	557.00	507.00
256 K-bit	32	TSOP 64K (8192 x 8) 256K (32768 x 8) parallel FRAM memory with RTC		FM3808-SG	121-0800●	931.00	854.00	776.00

Compliant Non-compliant + Limited stock - RoHS replacement available
RoHS

300,000 products, stocked and ready to despatch

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